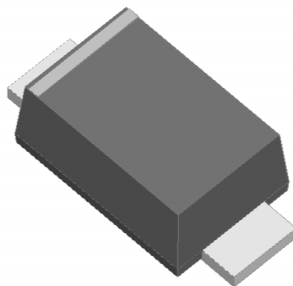


Features

LVF Schottky chip
Low VF, Low power losses, high efficiency
Ideal for surface mounted applications
Plastic Case Material has UL Flammability

Mechanical Data

Package: SMAF
Terminals: Tin Plated leads, solderable per
Mil-STD-750 Method 2026
Polarity: As marked
Molding compound meets UL 94 V-0 flammability rating,
ROHS-compliant



SMAF



Maximum Ratings (Ta=25°C Unless otherwise specified)

Type Number	SYMBOL	RBR5LAM60ATR-TP	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	60	V
Maximum RMS Voltage	V_{RMS}	42	V
Maximum DC Blocking Voltage	V_{DC}	60	V
Maximum Average Forward Rectified Current	$I_{O(AV)}$	5.0	A
Peak Forward Surge Current 8.3ms Single half-sine-wave superimposed on rated load (JEDEC Method) on rated	IFSM	100.0	A
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25°C		200.0	A
Current squared time @1ms ≤ t ≤ 8.3ms Tj=25°C, Rating of per diode	I^2t	41.5	A ² S
Maximum Forward Voltage at 5.0A DC	V_{FM}	0.55	V
Maximum Reverse Current TA = 25°C	IR	0.2	mA
at Rated DC Blocking Voltage TA = 80°C		50.0	
Typical Thermal Resistance Between junction and ambient	R_{QJA}	65.0	°C/W
Operating Junction Temperature Range	T_J	—55to+150	°C
Storage Temperature Range	T_{STG}	—55to+150	°C

FIG. 1 MAXIMUM AVERAGE FORWARD CURRENT DERATING

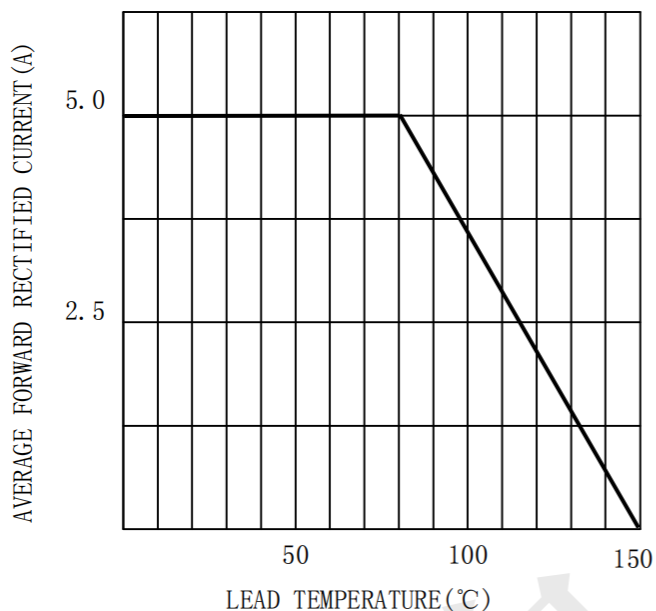


FIG. 2 TYPICAL FORWARD CHARACTERISTICS

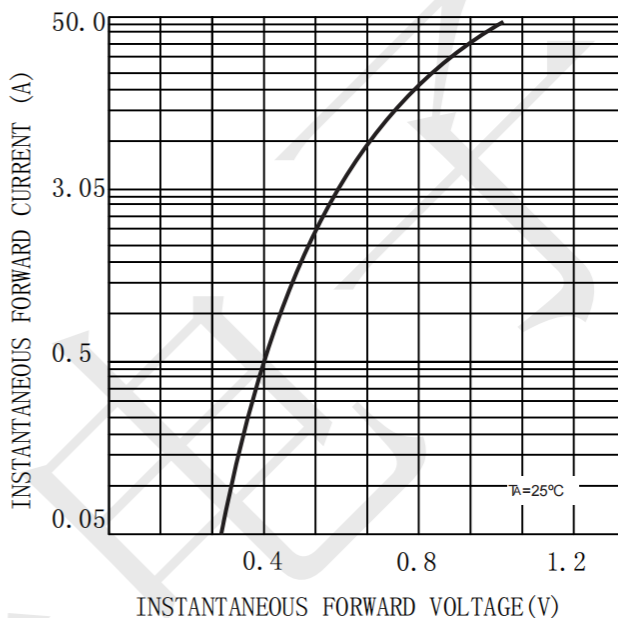


FIG. 3 MAXIMUM NON-REPEITIVE SURGE CURRENT

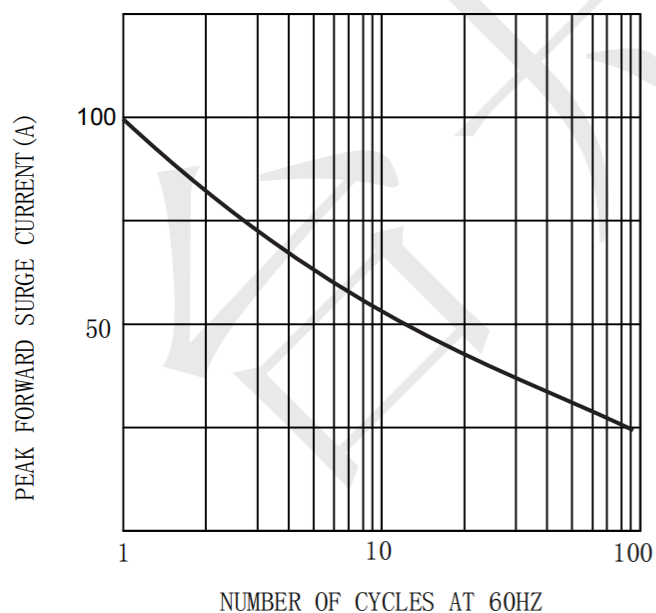
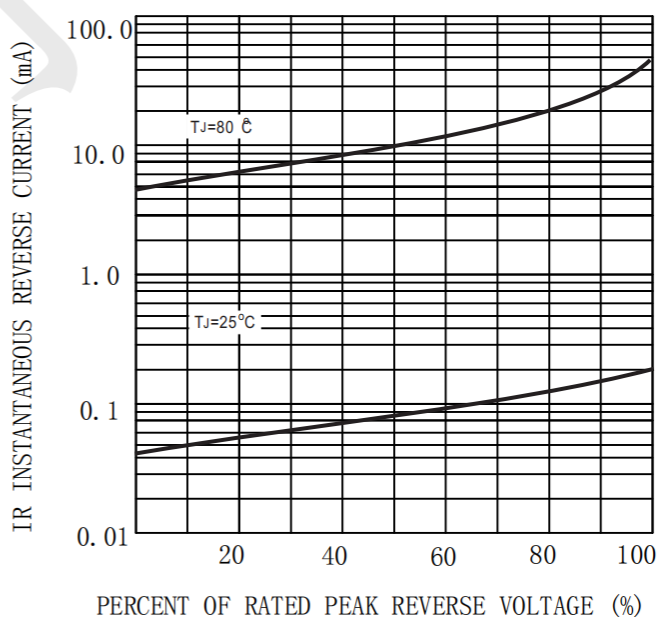
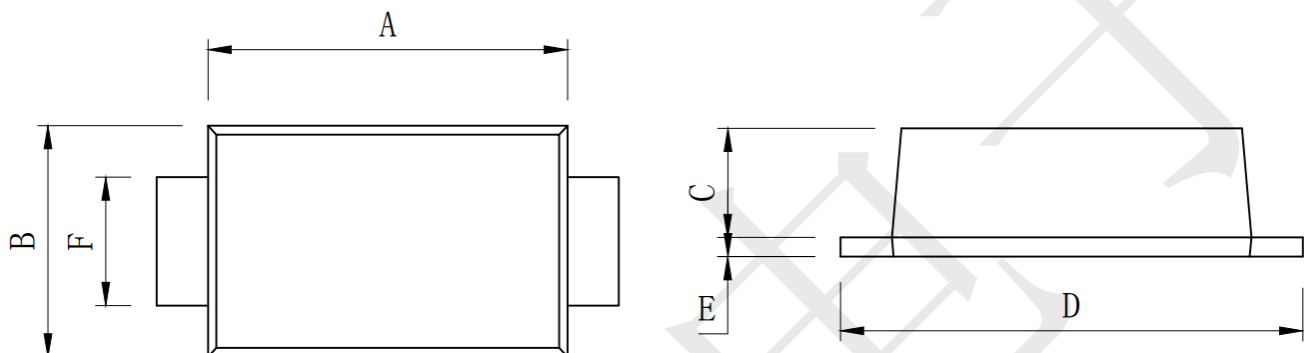


FIG. 4 TYPICAL REVERSE CHARACTERISTICS (per element)



Outline Dimensions

SMAF



SMAF				
DIM	INC HES		MM	
	MIN	MAX	MIN	MAX
A	0.13	0.15	3.2	3.8
B	0.09	0.11	2.3	2.7
C	0.03	0.05	0.8	1.2
D	0.16	0.20	4	5
E	/	0.01	/	0.3
F	0.04	0.08	1	2